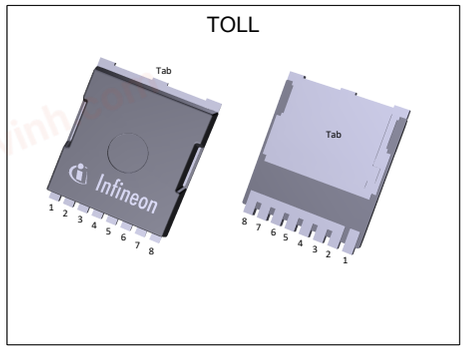
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MOSFET

StrongIRFET™ 2 Power-Transistor



Features

- Optimized for a wide range of applications
- N-Channel, normal level
- 100% avalanche tested
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

Product validation

Qualified according to JEDEC Standard

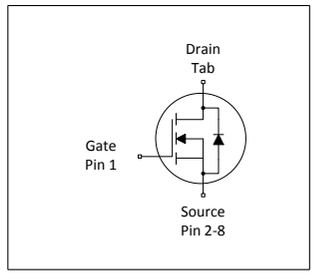


Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	100	V
$R_{DS(on),max}$	2.25	mΩ
I_D	236	A
Q_{oss}	131	nC
Q_G	103	nC

Type / Ordering Code	Package	Marking	Related Links
IPT022N10NF2S	PG-HSOF-8	022N10NS	-

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1 Maximum ratings

at T_A=25 °C, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current[1]	I_D	- - - -	- - - -	236 167 148 29	A	V_{GS}=10 V, T_C=25 °C V_{GS}=10 V, T_C=100 °C V_{GS}=6 V, T_C=100 °C V_{GS}=10V,T_A=25°C,R_{thJA}=40°C/W[2]
Pulsed drain current[3]	$I_{D,pulse}$	-	-	944	A	T_A=25 °C
Avalanche energy, single pulse[4]	E_{AS}	-	-	150	mJ	I_D=130 A, R_{GS}=25 Ω
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	- -	- -	250 3.8	W	T_C=25 °C T_A=25 °C, R_{thJA}=40 °C/W[2]
Operating and storage temperature	T_j, T_{stg}	-55	-	175	°C	-

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	0.6	°C/W	-
Thermal resistance, junction - ambient, 6 cm² cooling area[2]	R_{thJA}	-	-	40	°C/W	-
Thermal resistance, junction - ambient, minimal footprint	R_{thJA}	-	-	62	°C/W	-

[1] Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature as specified. For other case temperatures please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.
[2] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.
[3] See Diagram 3 for more detailed information
[4] See Diagram 13 for more detailed information

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3 Electrical characteristics

at T_j=25 °C, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	100	-	-	V	V_{GS}=0 V, I_D=1 mA
Gate threshold voltage	$V_{GS(th)}$	2.2	3.0	3.8	V	V_{DS}=V_{GS}, I_D=169 µA
Zero gate voltage drain current	I_{DSS}	- -	0.1 10	1 100	µA	V_{DS}=100 V, V_{GS}=0 V, T_j=25 °C V_{DS}=100 V, V_{GS}=0 V, T_j=125 °C
Gate-source leakage current	I_{GSS}	-	10	100	nA	V_{GS}=20 V, V_{DS}=0 V
Drain-source on-state resistance	$R_{DS(on)}$	- -	2.0 2.5	2.25 2.9	mΩ	V_{GS}=10 V, I_D=150 A V_{GS}=6 V, I_D=75 A
Gate resistance	R_G	-	1.8	-	Ω	-
Transconductance[1]	g_{fs}	110	-	-	S	|V_{DS}|≥2|I_D|$R_{DS(on)max}$, I_D=100 A

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	7300	-	pF	V_{GS}=0 V, V_{DS}=50 V, f=1 MHz
Output capacitance	C_{oss}	-	1100	-	pF	V_{GS}=0 V, V_{DS}=50 V, f=1 MHz
Reverse transfer capacitance	C_{rss}	-	49	-	pF	V_{GS}=0 V, V_{DS}=50 V, f=1 MHz
Turn-on delay time	$t_{d(on)}$	-	20	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=100 A, $R_{G,ext}$=1.6 Ω
Rise time	t_r	-	65	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=100 A, $R_{G,ext}$=1.6 Ω
Turn-off delay time	$t_{d(off)}$	-	47	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=100 A, $R_{G,ext}$=1.6 Ω
Fall time	t_f	-	26	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=100 A, $R_{G,ext}$=1.6 Ω

Table 6 Gate charge characteristics[2]

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	34	-	nC	V_{DD}=50 V, I_D=100 A, V_{GS}=0 to 10 V
Gate charge at threshold	$Q_{g(th)}$	-	22	-	nC	V_{DD}=50 V, I_D=100 A, V_{GS}=0 to 10 V
Gate to drain charge	Q_{gd}	-	21	-	nC	V_{DD}=50 V, I_D=100 A, V_{GS}=0 to 10 V
Switching charge	Q_{sw}	-	33	-	nC	V_{DD}=50 V, I_D=100 A, V_{GS}=0 to 10 V
Gate charge total[1]	Q_g	-	103	155	nC	V_{DD}=50 V, I_D=100 A, V_{GS}=0 to 10 V
Gate plateau voltage	$V_{plateau}$	-	4.6	-	V	V_{DD}=50 V, I_D=100 A, V_{GS}=0 to 10 V
Output charge	Q_{oss}	-	131	-	nC	V_{DS}=50 V, V_{GS}=0 V

[1] Defined by design. Not subject to production test.
[2] See ″Gate charge waveforms″ for parameter definition

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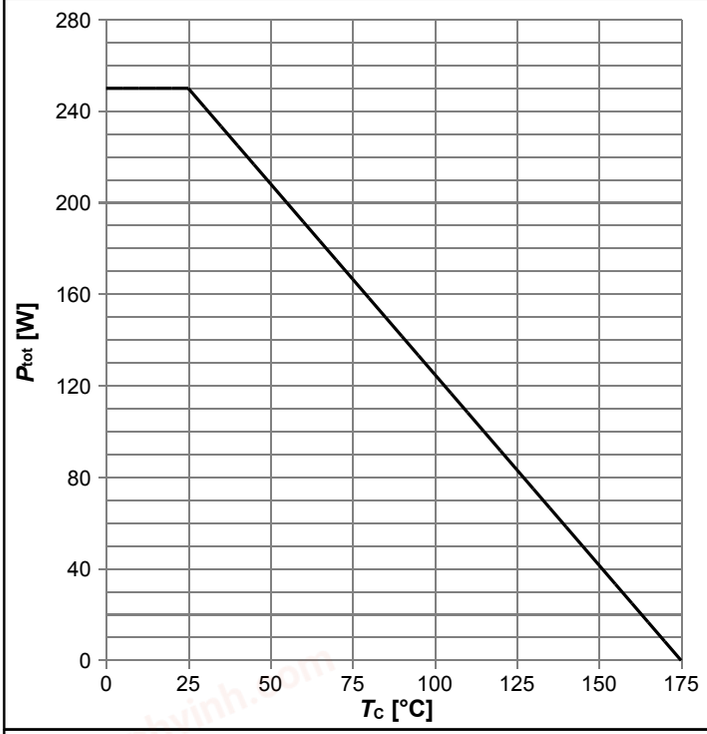
Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	182	A	T_C=25 °C
Diode pulse current	$I_{S,pulse}$	-	-	944	A	T_C=25 °C
Diode forward voltage	V_{SD}	-	0.87	1.2	V	V_{GS}=0 V, I_F=100 A, T_j=25 °C
Reverse recovery time	t_{rr}	-	44	-	ns	V_R=50 V, I_F=100 A, di_F/dt=500 A/µs
Reverse recovery charge	Q_{rr}	-	327	-	nC	V_R=50 V, I_F=100 A, di_F/dt=500 A/µs

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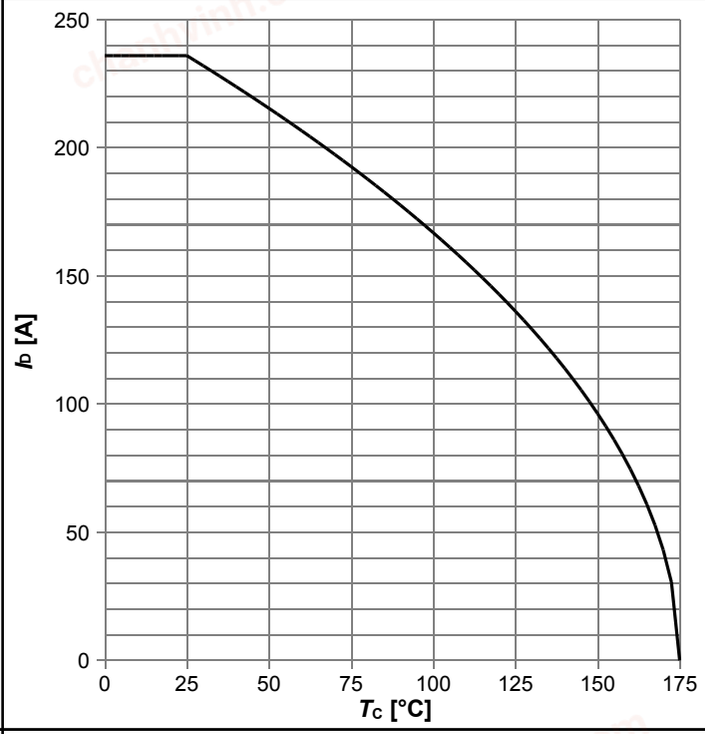
4 Electrical characteristics diagrams

Diagram 1: Power dissipation



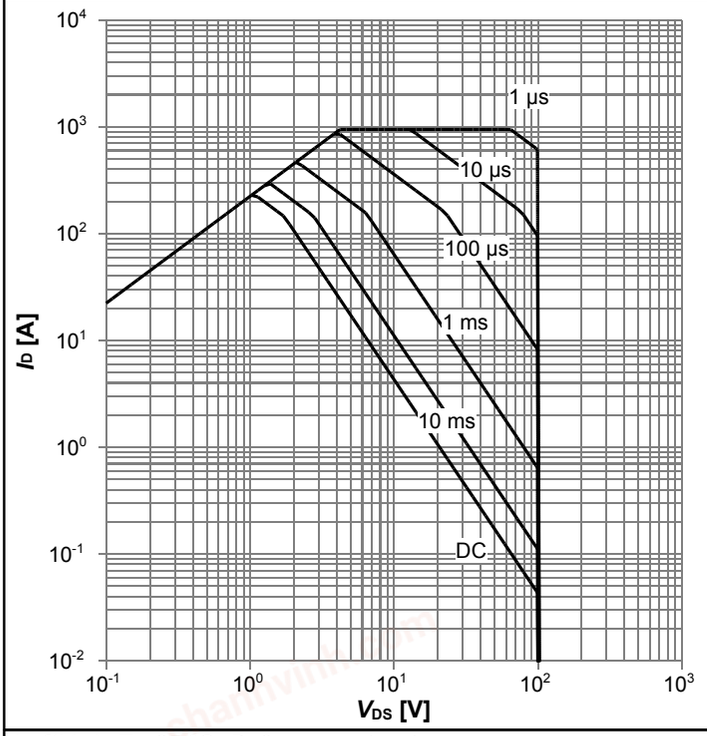
$P_{tot}=f(T_C)$

Diagram 2: Drain current



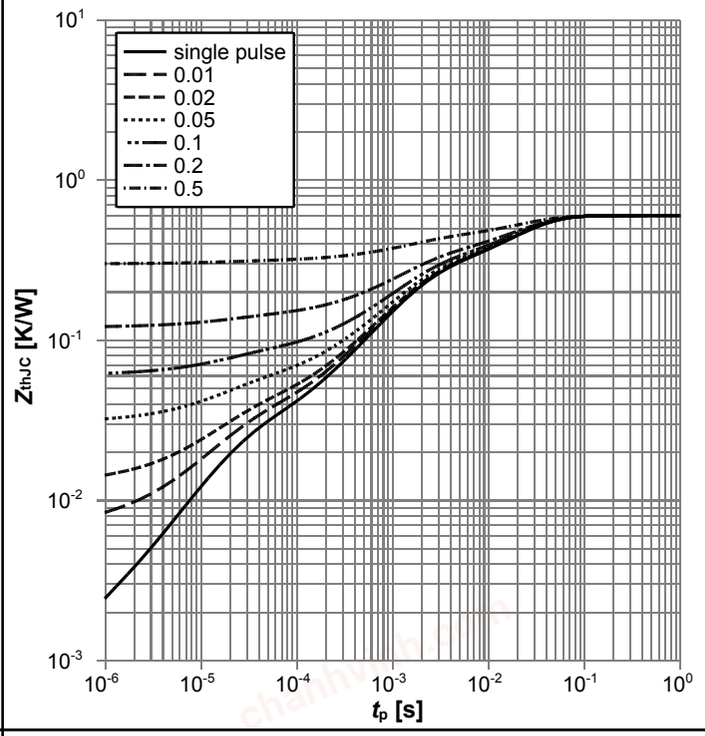
$I_D=f(T_C)$; $V_{GS}\geq 10$ V

Diagram 3: Safe operating area



$I_D=f(V_{DS})$; $T_C=25$ °C; $D=0$; parameter: t_p

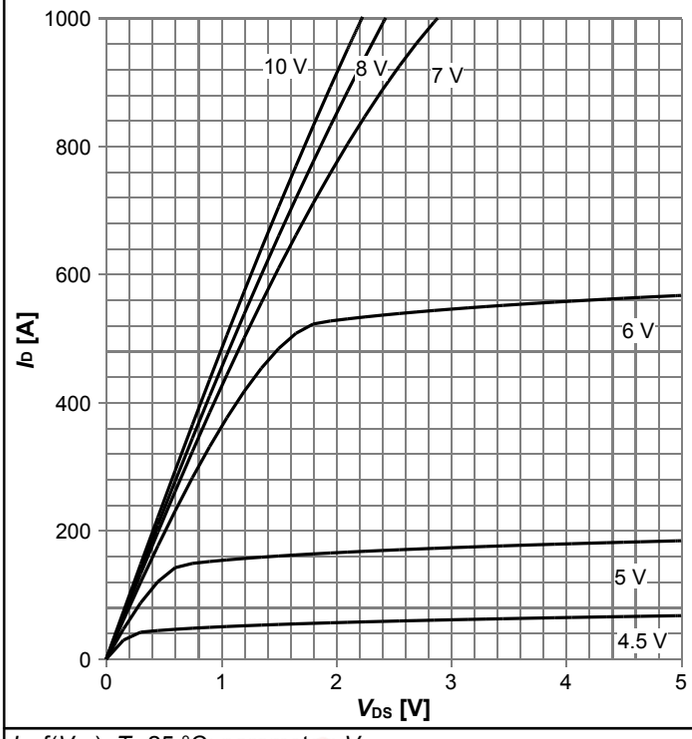
Diagram 4: Max. transient thermal impedance



$Z_{thJC}=f(t_p)$; parameter: $D=t_p/T$

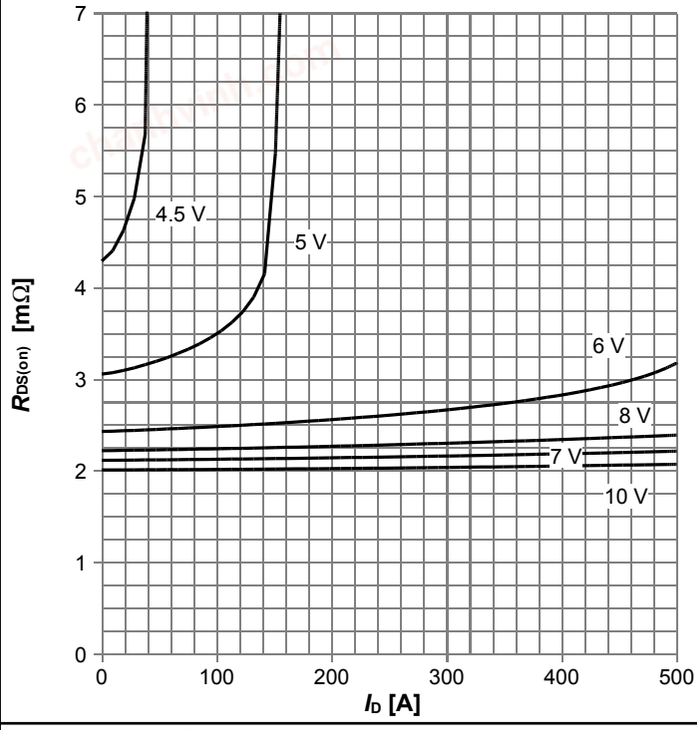
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Diagram 5: Typ. output characteristics



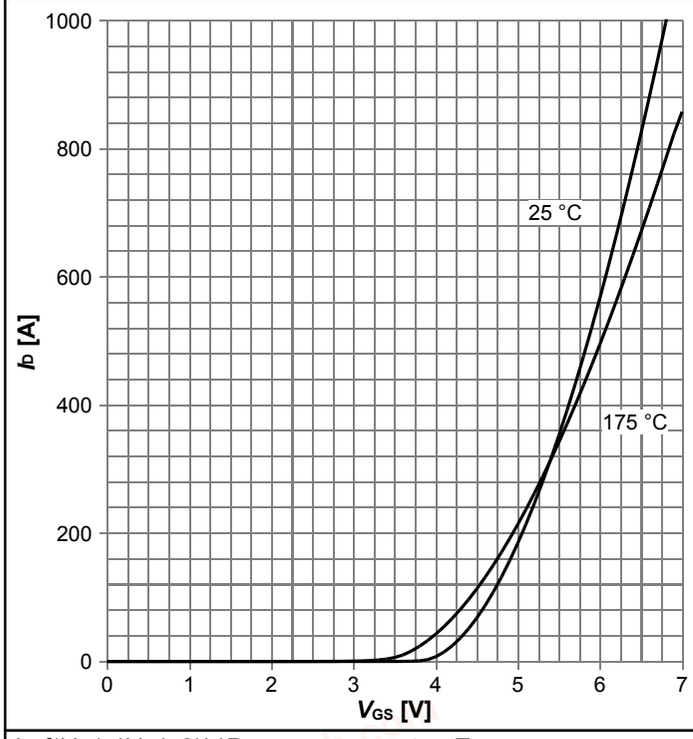
$I_D=f(V_{DS})$, $T_j=25$ °C; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



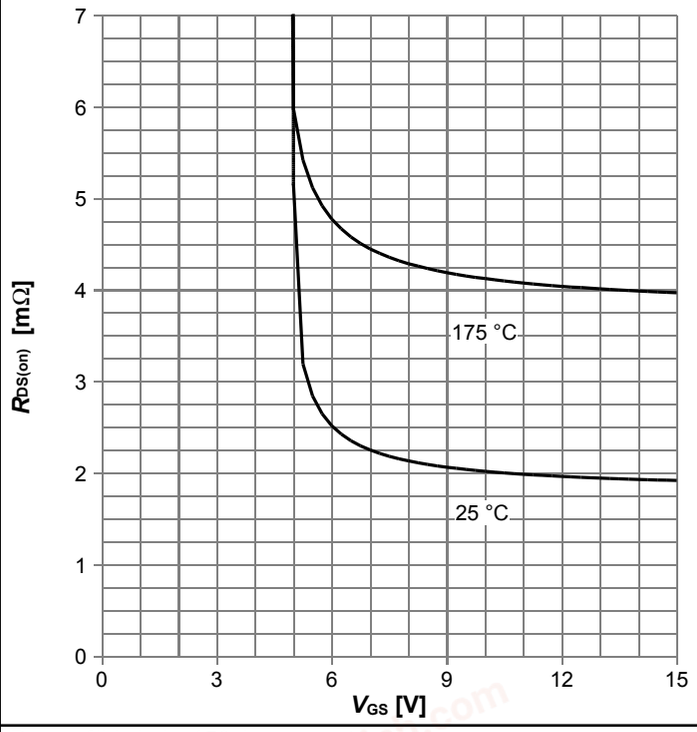
$R_{DS(on)}=f(I_D)$, $T_j=25$ °C; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



$I_D=f(V_{GS})$, $|V_{DS}|>2|I_D|R_{DS(on)max}$; parameter: T_j

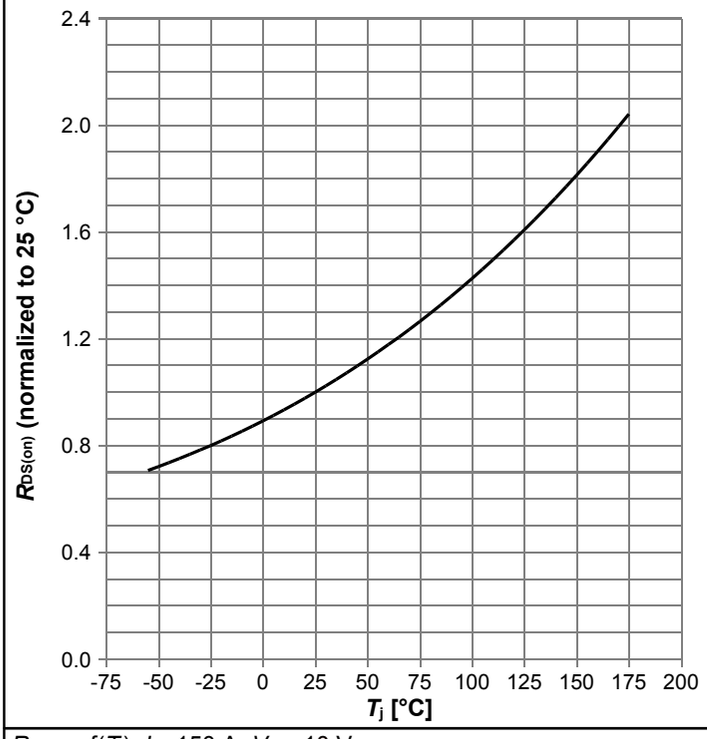
Diagram 8: Typ. drain-source on resistance



$R_{DS(on)}=f(V_{GS})$, $I_D=150$ A; parameter: T_j

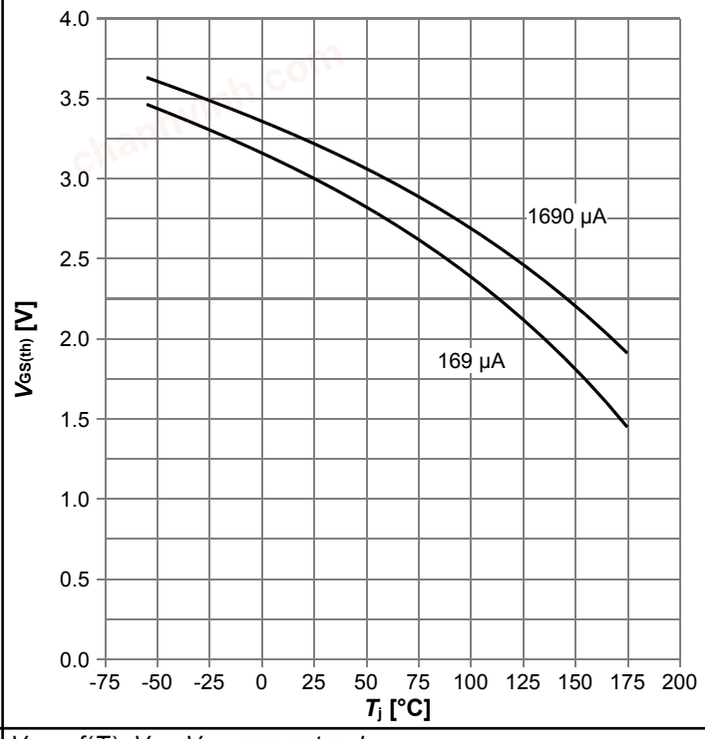
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Diagram 9: Normalized drain-source on resistance



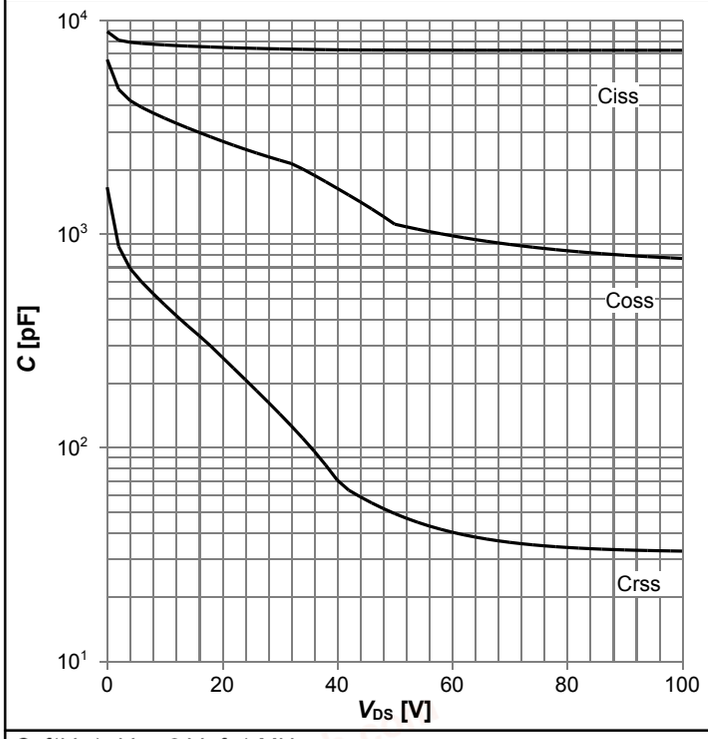
$R_{DS(on)}$=f(T_j), I_D=150 A, V_{GS}=10 V

Diagram 10: Typ. gate threshold voltage



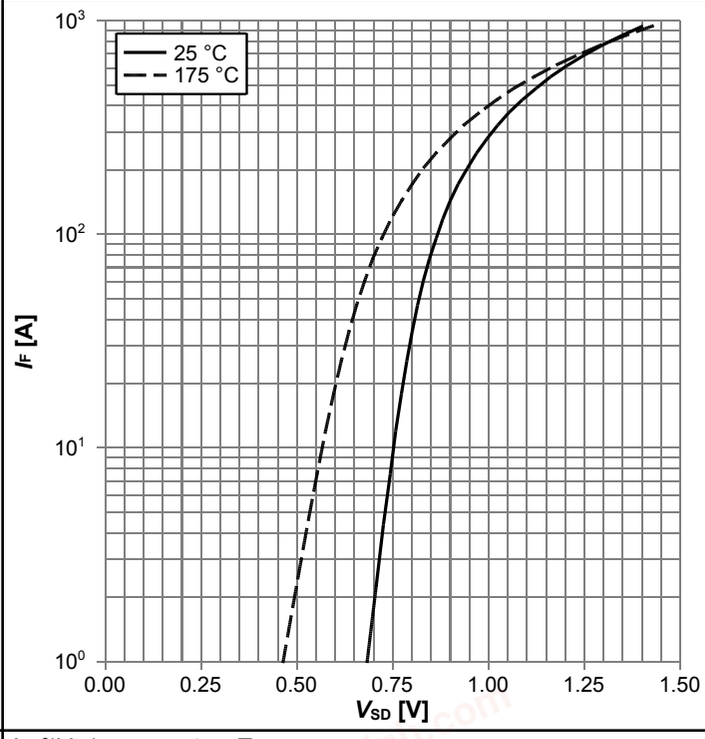
$V_{GS(th}$=f(T_j), V_{GS}=V_{DS}; parameter: I_D

Diagram 11: Typ. capacitances



C=f(V_{DS}); V_{GS}=0 V; f=1 MHz

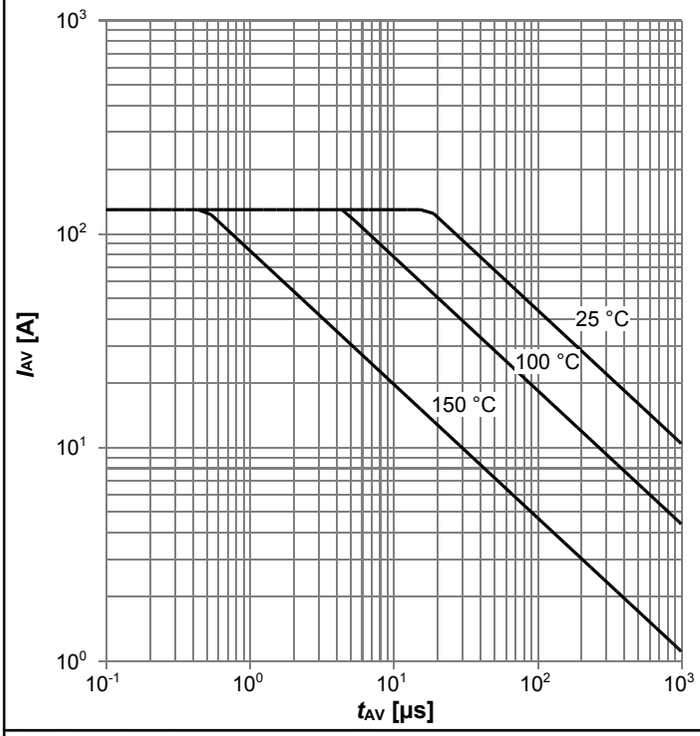
Diagram 12: Typ. forward characteristics of reverse diode



I_F=f(V_{SD}); parameter: T_j

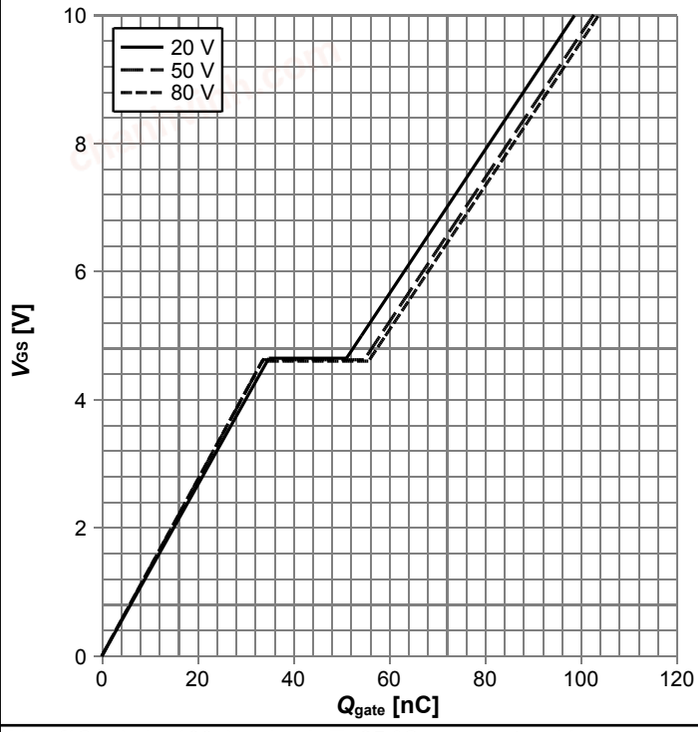
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Diagram 13: Avalanche characteristics



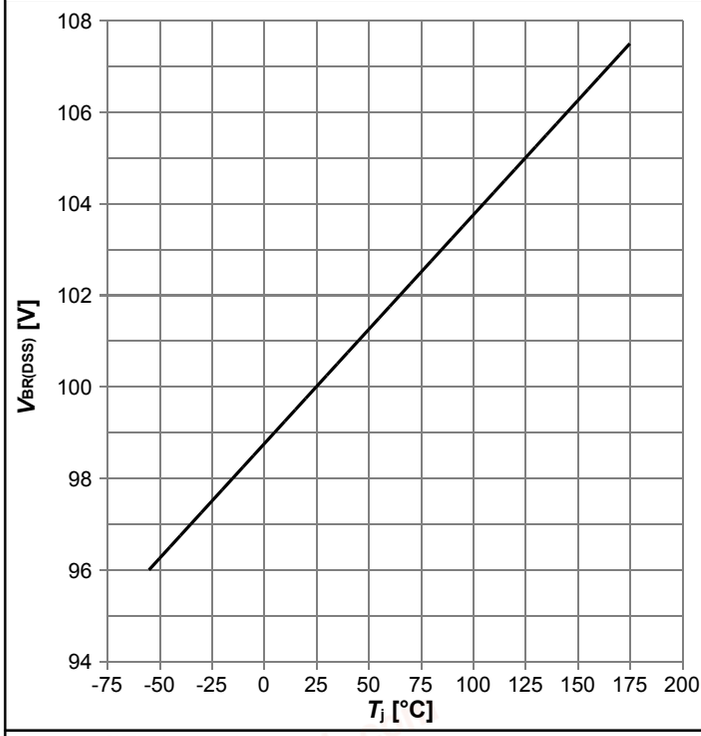
I_{AS}=f(t_{AV}); R_{GS}=25 Ω; parameter: $T_{j,start}$

Diagram 14: Typ. gate charge



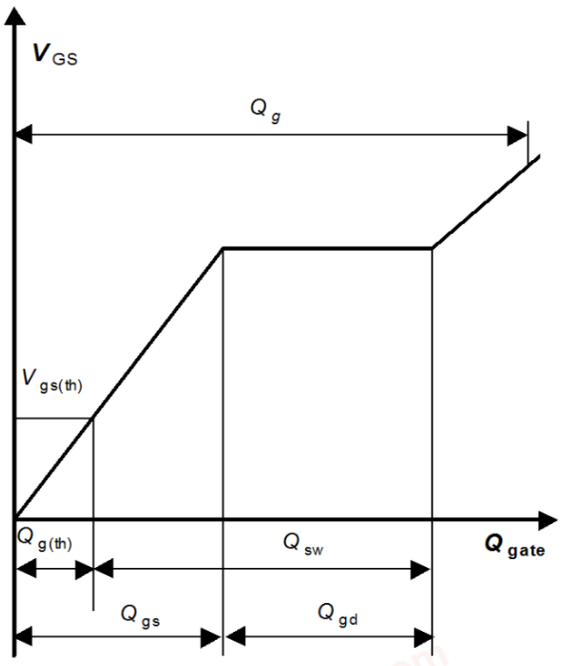
V_{GS}=f(Q_{gate}), I_D=100 A pulsed, T_j=25 °C; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage



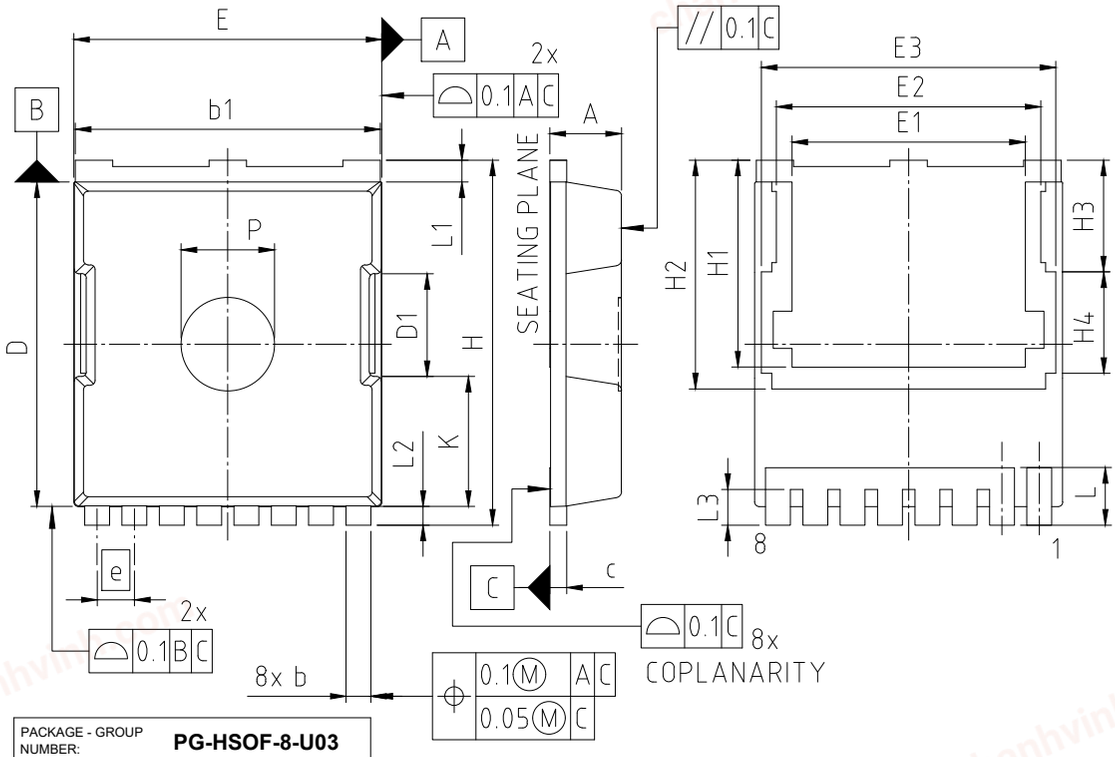
$V_{BR(DSS)}$=f(T_j); I_D=1 mA

Diagram Gate charge waveforms



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5 Package Outlines



PACKAGE - GROUP NUMBER:	PG-HSOF-8-U03	
DIMENSIONS	**MILLIMETERS**	
	MIN.	MAX.
A	2.20	2.40
b	0.70	0.90
b1	9.70	9.90
c	0.40	0.60
D	10.28	10.58
D1	3.15	3.45
E	9.70	10.10
E1	7.35	7.65
E2	8.50	
E3	9.46	
e	1.20 (BSC)	
H	11.48	11.98
H1	6.55	6.95
H2	7.35	
H3	3.59	
H4	3.26	
N	8	
K	4.03	4.33
L	1.60	2.10
L1	0.55	0.85
L2	0.45	0.75
L3	1.00	1.30
P	2.90	3.10

Note 1: Lead length up to anti flash profile, mold flashes excluded.

Figure 1 Outline PG-HSOF-8, dimensions in mm

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Revision History

IPT022N10NF2S

Revision: 2022-08-08, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2022-07-20	Release of final version
2.1	2022-08-08	Update current Rds(on)

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